

ABSTRACT OF THE DISCLOSURE

The disclosure relates to a Fin field effect transistor (FinFET). An exemplary structure for a FinFET comprises a substrate comprising a top surface; a first fin and a second fin extending above the substrate top surface, wherein each of the fins has a top surface and sidewalls; an insulation layer between the first and second fins extending part way up the fins from the substrate top surface; a first gate dielectric covering the top surface and sidewalls of the first fin having a first thickness and a second gate dielectric covering the top surface and sidewalls of the second fin having a second thickness less than the first thickness; and a conductive gate strip traversing over both the first gate dielectric and second gate dielectric.

Figure 6